



P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(th)} < 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

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Top View

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42
 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)







Drain

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP2004WK-7	SOT323	3000/Tape & Reel		

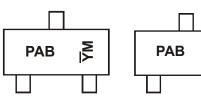
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

Notes:

3. Halogen - and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



PAB = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Year	2007	2008	2009	2010	201	1 20)12	2013	2	2014	2015	2016	2017
Code	U	V	W	Х	Y		Z	А		В	С	D	E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Ju	I A	ug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7		8	Q	0	N	П

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Shanghai A/T Site

See http://www and Lead-free.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (Note 5)	I _D	-400	mA
Pulsed Drain Current	I _{DM}	-1.4	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	Pd	250	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	500	°C/W
Operating and Storage Temperature Range	T _{j,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

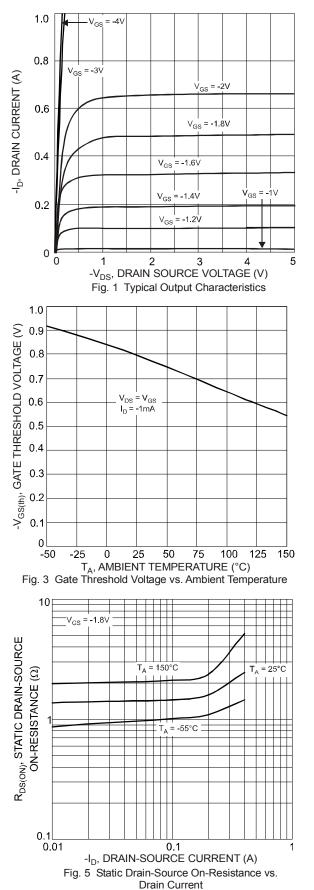
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)			•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			0.7	0.9		V _{GS} = -4.5V, I _D = -430mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.1 1.7	1.4 2.0	Ω	V _{GS} = -2.5V, I _D = -300mA
						V _{GS} = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	200			mS	V _{DS} =10V, I _D = -0.2A
Diode Forward Voltage (Note 6)	V _{SD}	-0.5		-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS (Note 7)	·		•	•		·
Input Capacitance	Ciss	_		175	pF	
Output Capacitance	C _{oss}	_		30	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	—	20	pF	

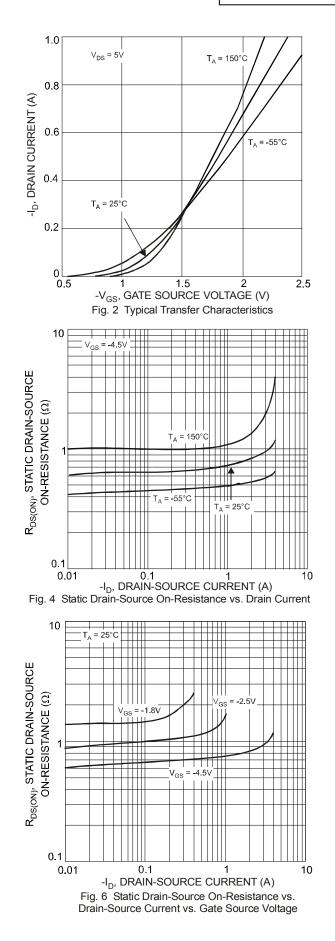
Notes:

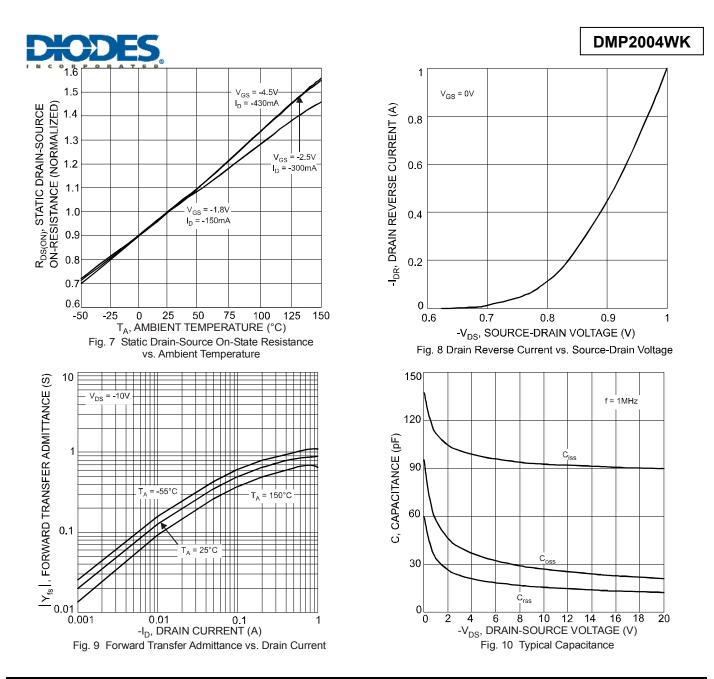
Device mounted on FR-4 PCB.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

DMP2004WK



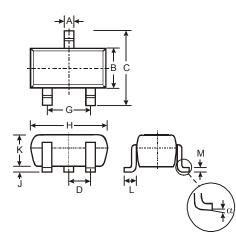






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

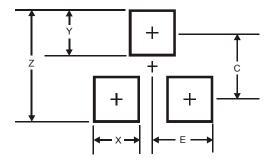


SOT323						
Dim	Min	Max	Тур			
Α	0.25	0.40	0.30			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	-	-	0.65			
G	1.20	1.40	1.30			
Н	1.80	2.20	2.15			
J	0.0	0.10	0.05			
Κ	0.90	1.00	0.95			
L	0.25	0.40	0.30			
М	0.10	0.18	0.11			
α	0°	8°	-			
All	Dimens	ions in	mm			



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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